

CAPACITORS OF SEMICONDUCTOR DEVICES INCLUDING  
SILICON-GERMANIUM AND METALLIC ELECTRODES AND METHODS OF  
FABRICATING THE SAME

Abstract of the Disclosure

5           A capacitor of a semiconductor device includes a cylinder type capacitor  
lower electrode, a dielectric layer, and an upper electrode. The upper electrode  
includes a metallic layer on the dielectric layer and a doped polySi<sub>1-x</sub>Ge<sub>x</sub> layer  
stacked on the metallic layer. Methods of forming these capacitors also are  
provided.

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